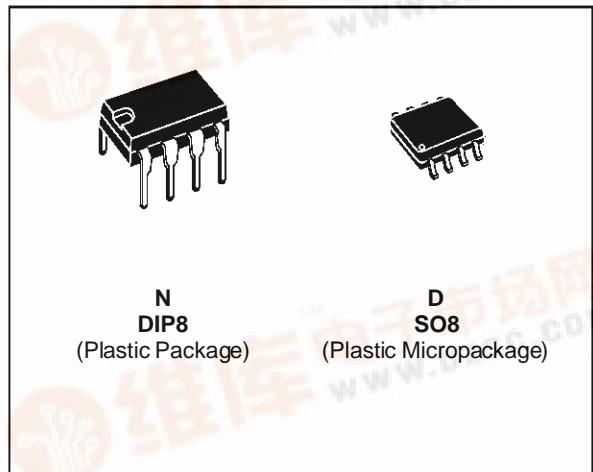




LF151 LF251 - LF351

WIDE BANDWIDTH SINGLE J-FET OPERATIONAL AMPLIFIER

- INTERNALLY ADJUSTABLE INPUT OFFSET VOLTAGE
- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : $16V/\mu s$ (typ)



DESCRIPTION

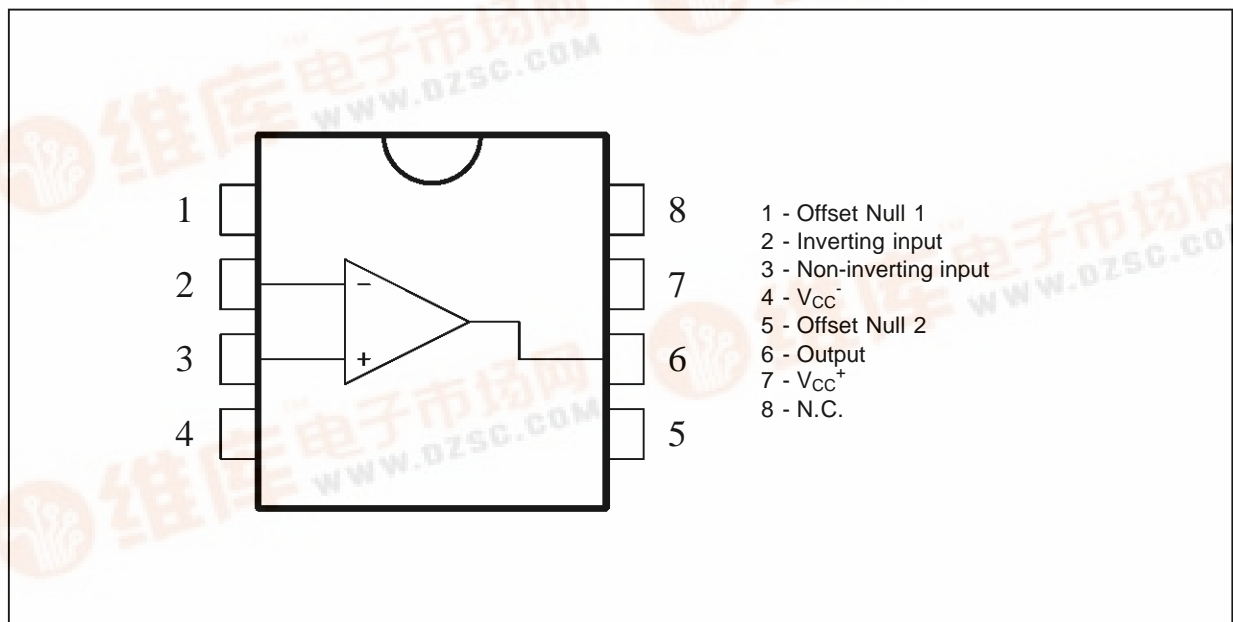
These circuits are high speed J-FET input single operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

ORDER CODES

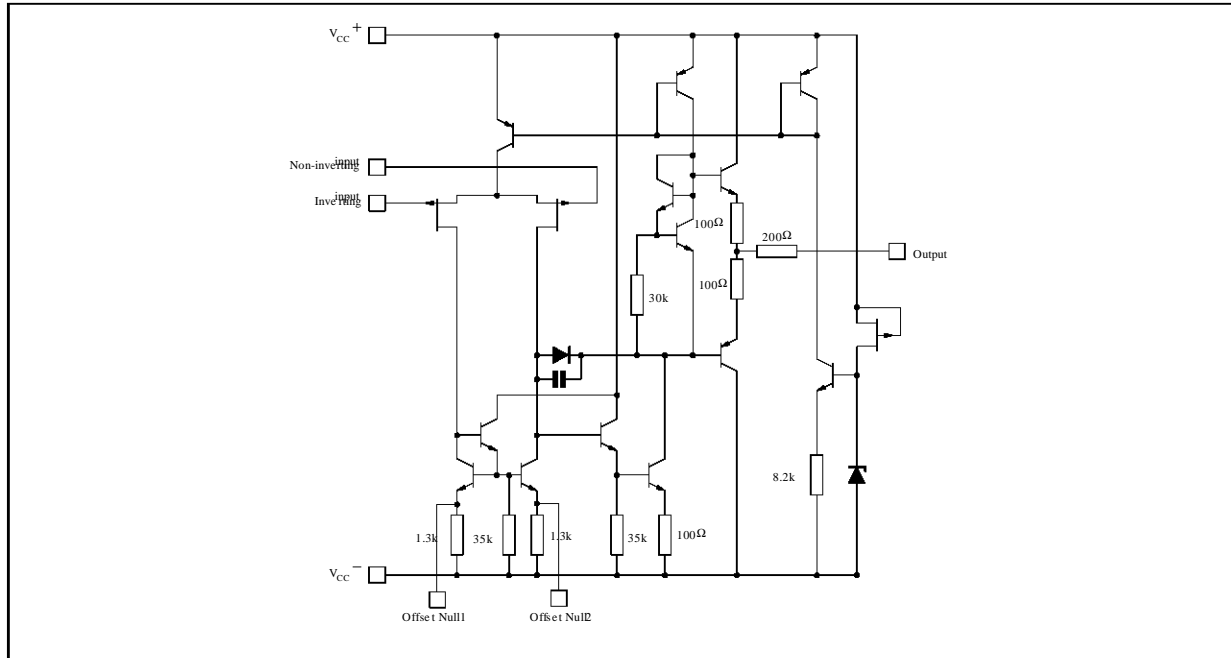
Part Number	Temperature	Package	
		N	D
LF351	0°C, +70°C	•	•
LF251	-40°C, +105°C	•	•
LF151	-55°C, +125°C	•	•

PIN CONNECTIONS (top view)

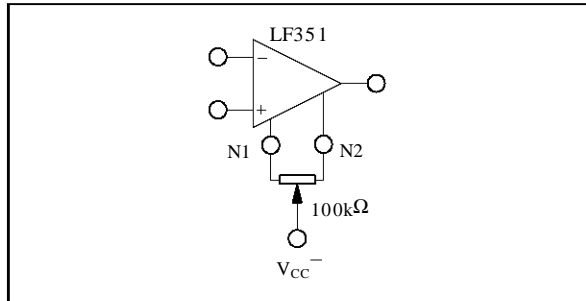


LF151 - LF251 - LF351

SCHEMATIC DIAGRAM



INPUT OFFSET VOLTAGE NULL CIRCUITS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage - (note 1)	± 18	V	
V_i	Input Voltage - (note 3)	± 15	V	
V_{id}	Differential Input Voltage - (note 2)	± 30	V	
P_{tot}	Power Dissipation	680	mW	
	Output Short-circuit Duration - (note 4)	Infinite		
T_{oper}	Operating Free Air Temperature Range	LF351 LF251 LF151	0 to 70 -40 to 105 -55 to 125	$^{\circ}C$
T_{stg}	Storage Temperature Range		-65 to 150	$^{\circ}C$

- Notes :**
1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}^+ and V_{CC}^- .
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
 4. The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

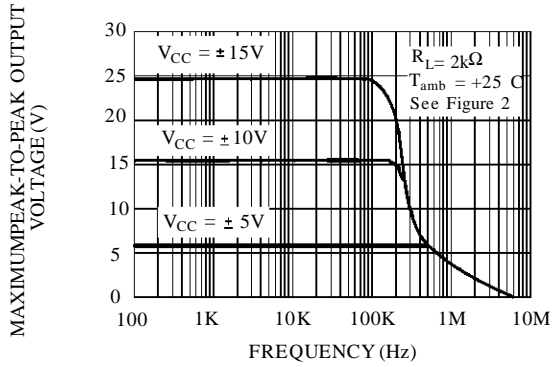
ELECTRICAL CHARACTERISTICS

V_{CC} = ±15V, T_{amb} = 25°C (unless otherwise specified)

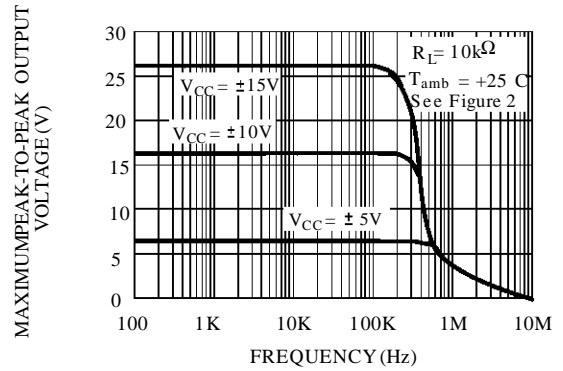
Symbol	Parameter	LF151 - LF251 - LF351			Unit
		Min.	Typ.	Max.	
V _{io}	Input Offset Voltage (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		3	10 13	mV
DV _{io}	Input Offset Voltage Drift		10		μV/°C
I _{io}	Input Offset Current * T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		5	100 4	pA nA
I _{ib}	Input Bias Current * T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		20	200 20	pA nA
A _{vd}	Large Signal Voltage Gain (R _L = 2kΩ, V _O = ±10V) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	50 25	200		V/mV
SVR	Supply Voltage Rejection Ratio (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	80 80	86		dB
I _{CC}	Supply Current (no load) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		1.4	3.4 3.4	mA
V _{icm}	Input Common Mode Voltage Range	±11	+15 -12		V
CMR	Common Mode Rejection Ratio (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	70 70	86		dB
I _{os}	Output Short-circuit Current T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	10 10	40	60 60	mA
±V _{OPP}	Output Voltage Swing T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	10 12 10 12	12 13.5		V
SR	Slew Rate (V _i = 10V, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)	12	16		V/μs
t _r	Rise Time (V _i = 20mV, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)		0.1		μs
K _{OV}	Overshoot (V _i = 20mV, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)		10		%
GBP	Gain Bandwidth Product (f = 100kHz, T _{amb} = 25°C, V _{in} = 10mV, R _L = 2kΩ, C _L = 100pF)	2.5	4		MHz
R _i	Input Resistance		10 ¹²		Ω
THD	Total Harmonic Distortion (f = 1kHz, A _V = 20dB, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, V _O = 2V _{PP})		0.01		%
e _n	Equivalent Input Noise Voltage (f = 1kHz, R _S = 100Ω)		15		$\frac{nV}{\sqrt{Hz}}$
∅ _m	Phase Margin		45		Degrees

* The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature.

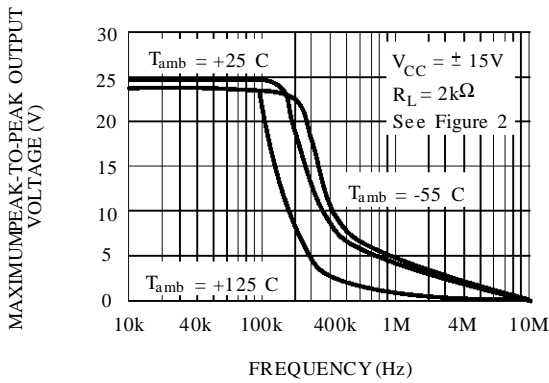
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



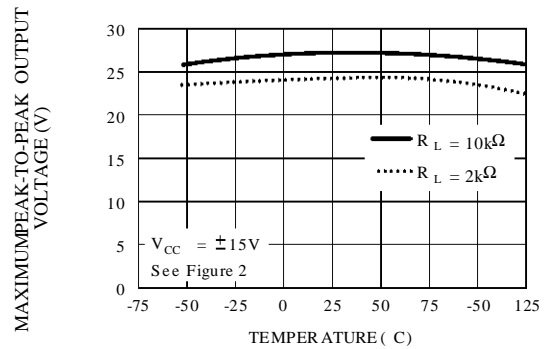
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



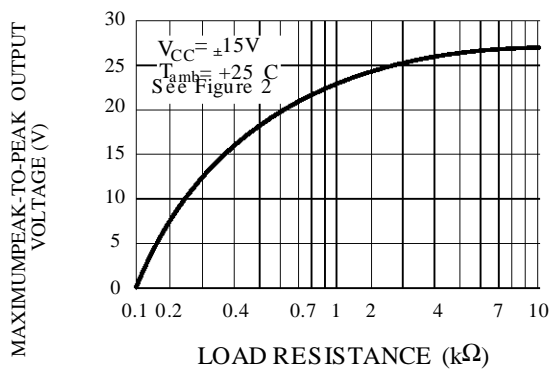
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



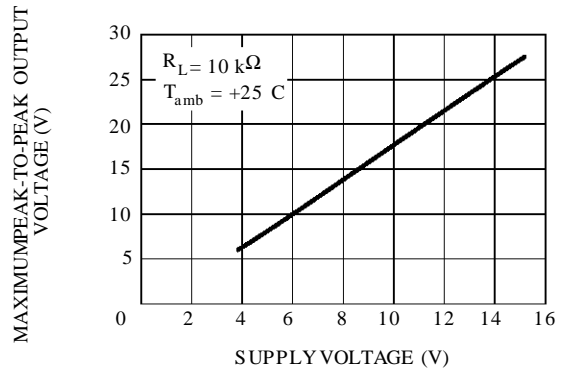
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



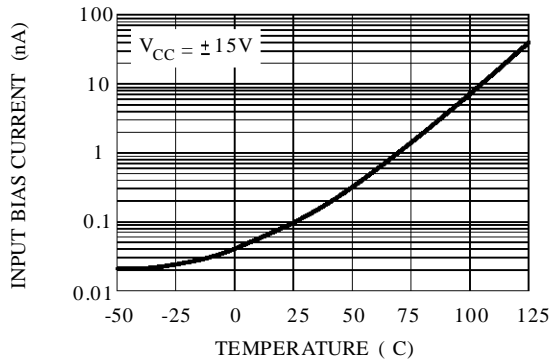
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE



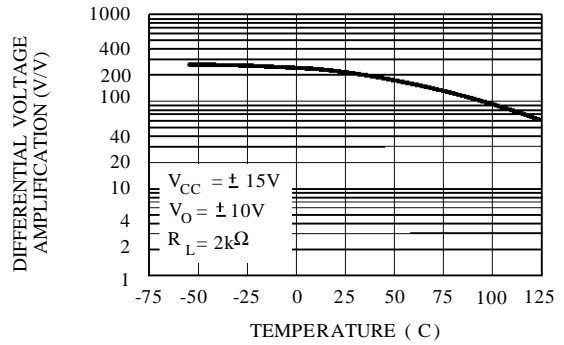
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE



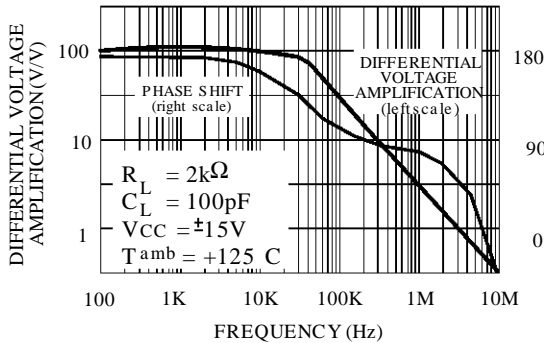
INPUT BIAS CURRENT VERSUS FREE AIR TEMPERATURE



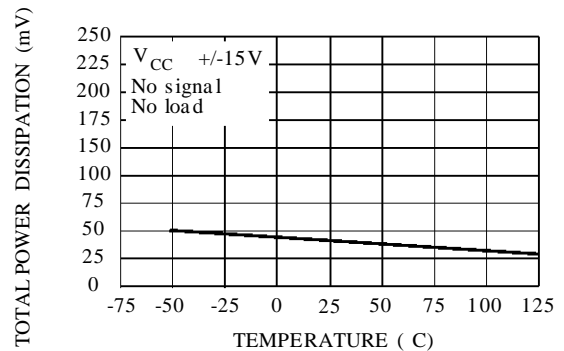
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VERSUS FREE AIR TEMPERATURE



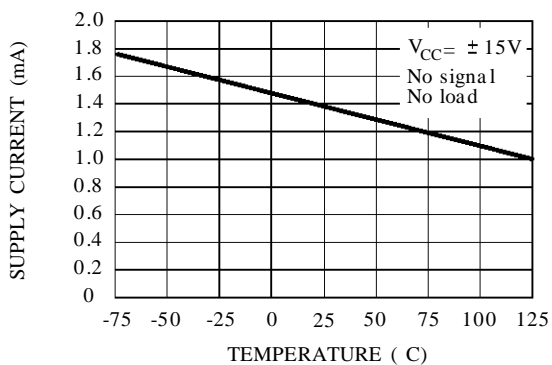
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VERSUS FREQUENCY



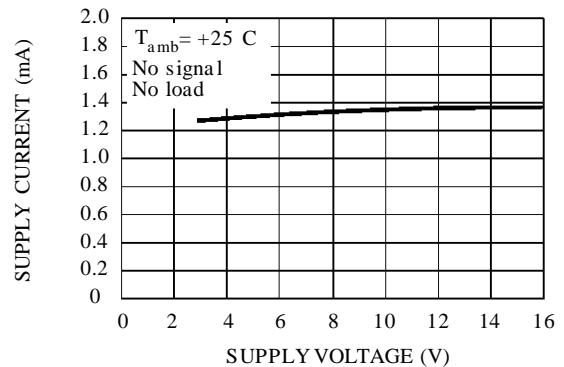
TOTAL POWER DISSIPATION VERSUS FREE AIR TEMPERATURE



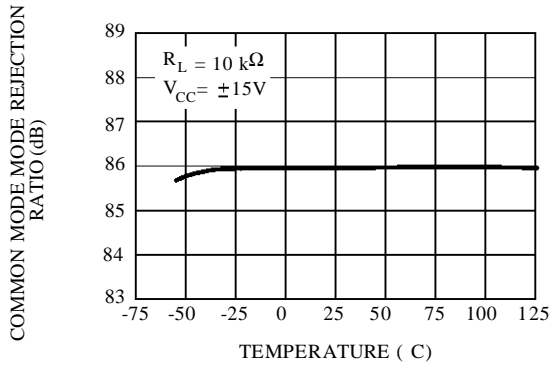
SUPPLY CURRENT PER AMPLIFIER VERSUS FREE AIR TEMPERATURE



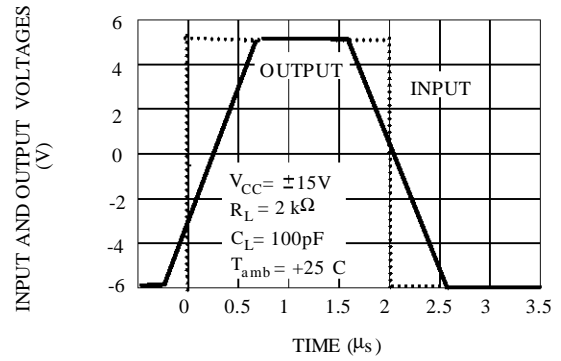
SUPPLY CURRENT PER AMPLIFIER VERSUS SUPPLY VOLTAGE



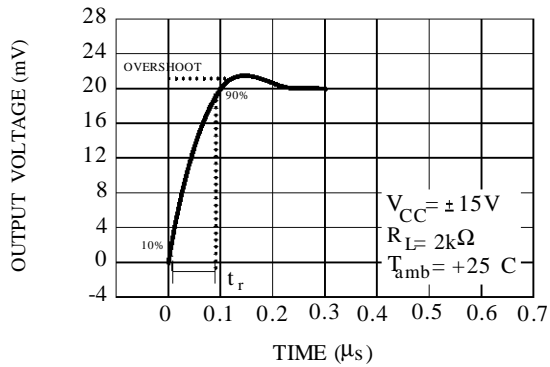
COMMON MODE REJECTION RATIO VERSUS FREE AIR TEMPERATURE



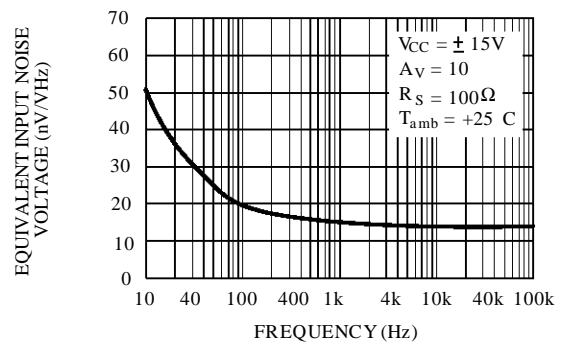
VOLTAGE FOLLOWER LARGE SIGNAL PULSE RESPONSE



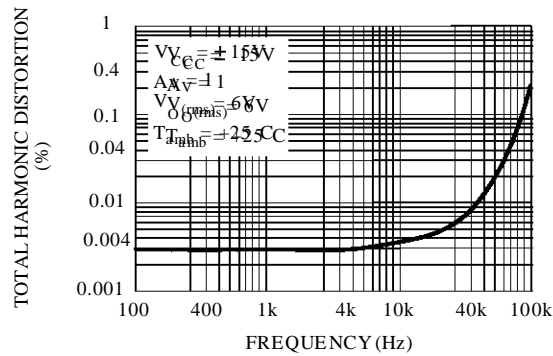
OUTPUT VOLTAGE VERSUS ELAPSED TIME



EQUIVALENT INPUT NOISE VOLTAGE VERSUS FREQUENCY



TOTAL HARMONIC DISTORTION VERSUS FREQUENCY



PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

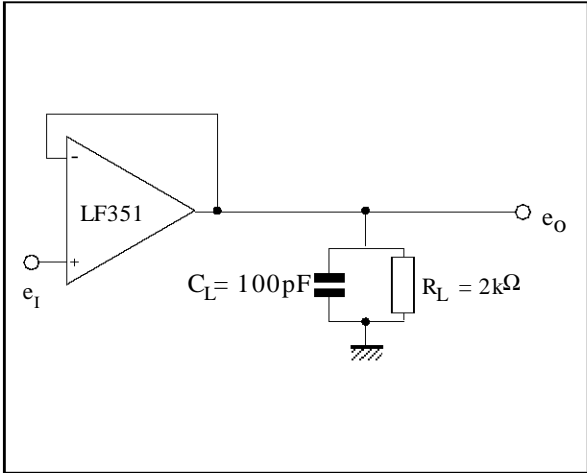
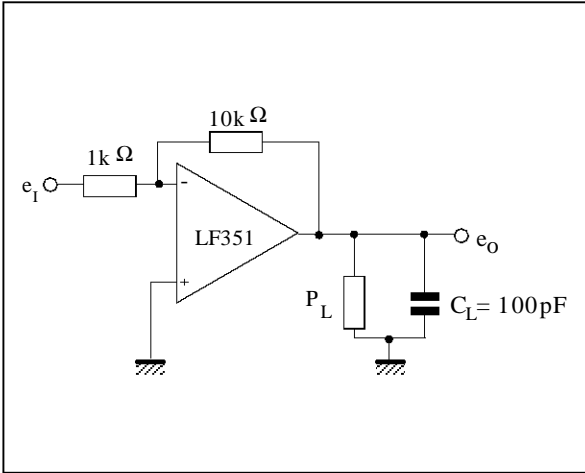
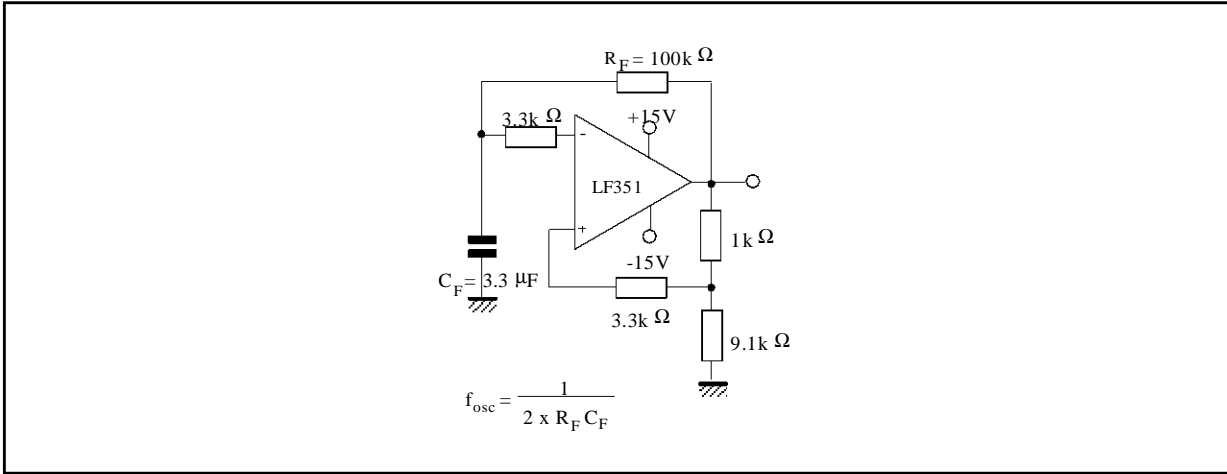


Figure 2 : Gain-of-10 Inverting Amplifier

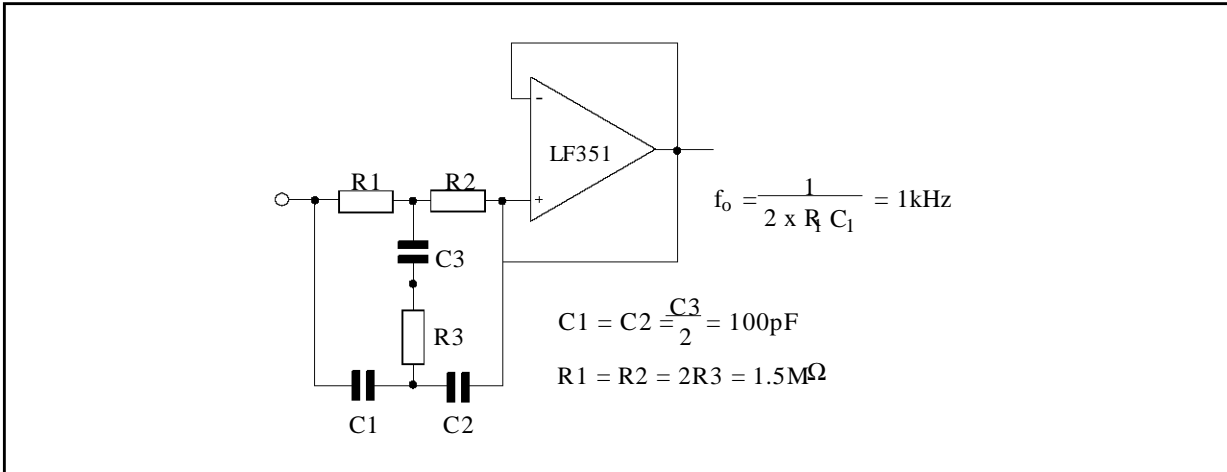


TYPICAL APPLICATION

(0.5Hz) SQUARE WAVE OSCILLATOR



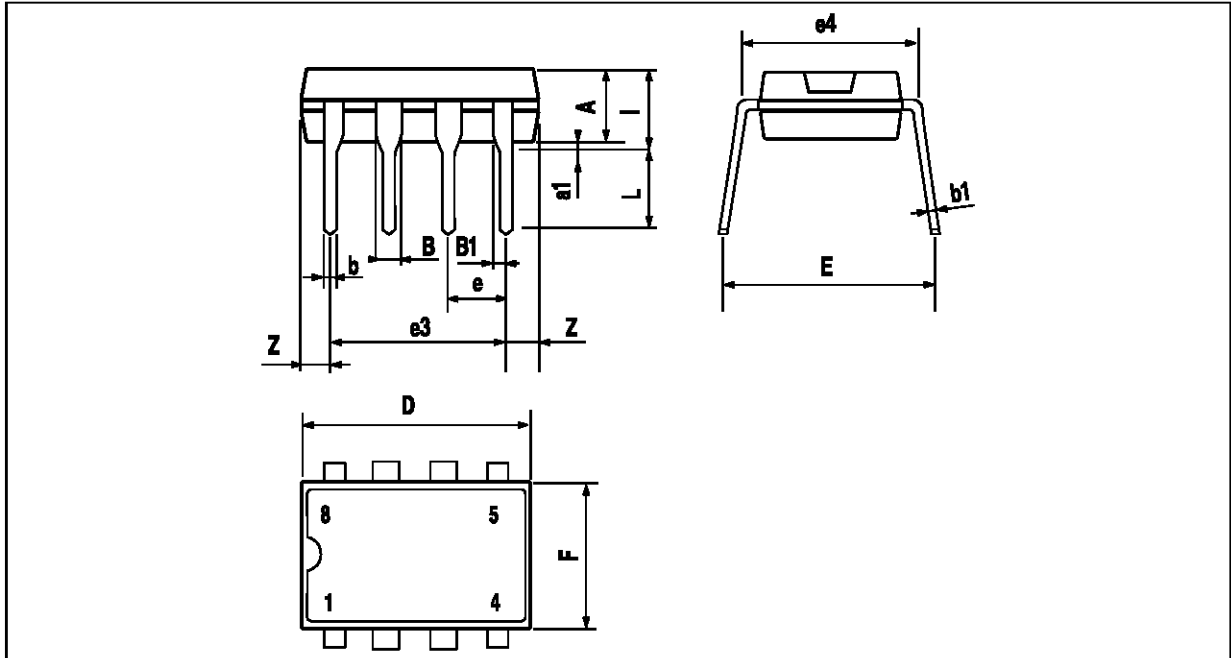
HIGH Q NOTCH FILTER



LF151 - LF251 - LF351

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC DIP

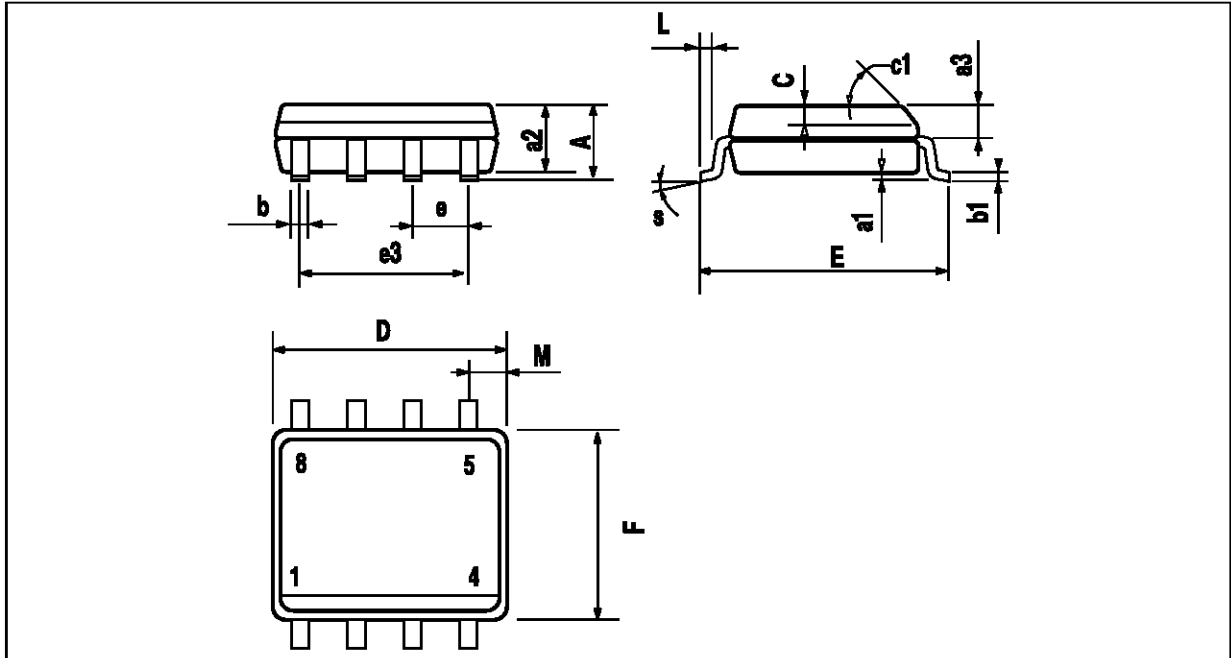


PM-DIP8E/PS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

DIP8.TBL

PACKAGE MECHANICAL DATA
8 PINS - PLASTIC MICROPACKAGE (SO)



PM-S08EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					

SO8:TBL

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1997 SGS-THOMSON Microelectronics – Printed in Italy – All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco
The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

ORDER CODE :